

ABSTRACT OF THE DISCLOSURE

A mesa-oxide isolation method comprises steps of placing a wafer in a metalorganic chemical vapor deposition (MOCVD) system or a molecular beam epitaxy (MBE) system to grow an epitaxial layer on a surface of 05 the wafer, spinning photo-resist on an upper surface of the epitaxial layer, exposing the wafer under a light to print electric circuit pattern on a masking and soaking the wafer in a developing solution to solve and remove the photosensitive resin, etching to remove a portion of 10 the epitaxial layer, growing an oxide layer on the area of the epitaxial layer without photo-resist by soaking the wafer in a chemical solution, removing photo-resist to form a mesa on the upper surface of the wafer, and depositing metal connections on the mesa and the wafer.